

Notice of References Cited	Application/Control No. 09/973,814	Applicant(s)/Patent Under Reexamination KUNIYASU ET AL.	
	Examiner Tuan N Nguyen	Art Unit 2828	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-6,285,695	09-2001	Asano et al.	372/45
	C	US-6,396,863	05-2002	Fukunaga, Toshiaki	372/46
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NON-PATENT DOCUMENTS

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	U	Horie et al. "Thermal Rollover Characteristics Up to 150 C of Buried-Stripe Type 980-nm Laser Diodes with a Current Injection Window Delineated by a SiN Layer", IEEE Photonics Technology Letters, Vol. 12, No.1. January 2000.
	V	Toshiaki FUKUNAGA et al. "High-power 0.8 um InGaAsP/InGaP/AlGaAs Single Quantum Well Lasers with Tensile-strained InGaP Barriers XP 001096289, Japanese Journal of Applied Physics. vol. 38, no. 4A. April 1, 1999
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.